

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device having a pixel matrix circuit that includes a pixel TFT and a storage capacitor:

wherein the pixel TFT has a channel formation region formed over a first wiring line with a first insulating layer interposed therebetween, and has a low concentration impurity region that is in contact with the channel formation region and overlaps the first wiring line;

wherein a gate electrode is formed over the channel formation region with a second insulating layer interposed therebetween;

wherein the gate electrode does not overlap the low concentration impurity region;

wherein the storage capacitor is formed:

from a capacitor wiring line,

from a semiconductor region that has the same composition as the channel formation region or the low concentration impurity region, and

from a part of the first insulating layer; [[and]]

wherein the first wiring line and the capacitor wiring line are formed on the same layer, and

wherein the shortest distance between the channel formation region and the first wiring line is longer than the shortest distance between the capacitor wiring line and the semiconductor region.

2. – 3. (Canceled)

4. (Previously Presented) A semiconductor device according to claim 1,

wherein the first wiring line is appropriately a conductive film mainly containing an element selected from the group consisting of tantalum (Ta), chromium (Cr), titanium (Ti), tungsten (W), molybdenum (Mo), and silicon (Si), or an alloy film or silicide film containing the above elements in combination, or a laminate of the conductive films, the alloy films, or the silicide films.

5. (Previously Presented) A semiconductor device according to claim 1,

wherein the channel formation region of the pixel TFT and the semiconductor region of the storage capacitor are formed of the same semiconductor layer.

6. (Previously Presented) A semiconductor device according to claim 1, wherein the first insulating layer is appropriately an oxide or halogenated compound containing an element selected from the group consisting of tantalum (Ta), titanium (Ti), barium (Ba), hafnium (Hf), bismuth (Bi), tungsten (W), thorium (Th), and lead (Pb).

7. (Previously Presented) A semiconductor device according to claim 1, wherein the first wiring line is in floating state.

8. (Previously Presented) A semiconductor device according to claim 1, wherein the first wiring line is kept at the lowest power supply electric potential.

9. (Currently Amended) A semiconductor device according to claim 1, wherein the pixel TFT is connected to [[the]] a source wiring line and [[the]] a gate wiring line, and the storage capacitor is formed under the source wiring line and/or the gate wiring line.

10. – 16. (Canceled)

17. (Previously Presented) A semiconductor device, wherein the semiconductor device according to claim 1 is an active matrix liquid crystal display or an active matrix EL display.

18. (Previously Presented) A semiconductor device, wherein the semiconductor device according to claim 1 is a video camera, a digital camera, a projector, a projection TV, a goggle type display, an automobile navigation system, a personal computer, or a portable information terminal.

19. (Previously Presented) A semiconductor device according to claim 1, wherein a cross section of the first wiring line is taper shape.

20. (Previously Presented) A semiconductor device according to claim 1, wherein a cross section of the capacitor wiring line is taper shape.

21. (Canceled).

22. (Previously Presented) The semiconductor device according to claim 1, wherein the insulating layer comprises a first insulating layer and a second insulating layer.

23. (Canceled)

24. (Canceled)

25. (Currently Presented) A semiconductor device according to claim 1, wherein the first wiring line and the gate electrode have the same electric potential.

26.- 61. (Canceled)